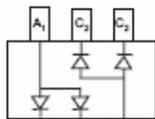
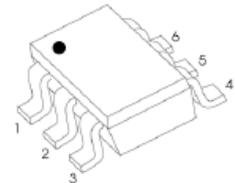
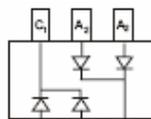
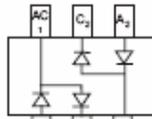
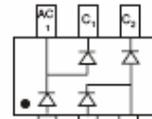
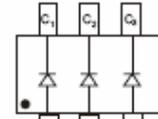


Plastic-Encapsulate Transistors

SCHOTTKY BARRIER DIODE ARRAYS

FEATURES

- Low Forward voltage drop
- Fast switching

SOT-363

BAS40DW-06
Marking: K46

BAS40DW-05
Marking: K45

BAS40DW-04
Marking: K44

BAS40BRW
Marking: K47

BAS40TW
Marking: K43

Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C

Parameter	Symbol	Limits	Unit
Non-Repetitive Peak reverse voltage	V_{RM}	40	V
DC Blocking Voltage	V_R		
Average Rectified Output Current	I_O	200	mA
Power Dissipation	P_d	200	mW
Thermal Resistance. Junction to Ambient Air	$R_{\theta JA}$	625	°C/W
Junction temperature	T_J	125	°C
Storage temperature range	T_{STG}	-65-125	°C

Electrical Ratings @Ta=25°C

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 10\mu A$	40		V
Reverse voltage leakage current	I_R	$V_R = 30V$		200	nA
Forward voltage	V_F	$I_F = 1mA$ $I_F = 40mA$		380 1000	mV
Total capacitance	C_T	$V_R = 0, f = 1MHz$		5	pF
Reverse recovery time	t_{rr}	$I_F = 10mA, I_R = I_F = 1mA$ $R_L = 100\Omega$		5	ns

Typical Characteristics

